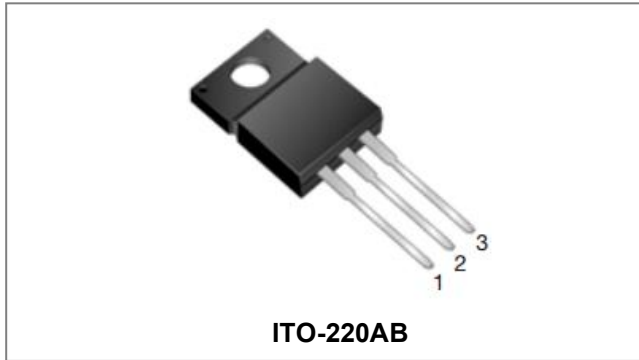


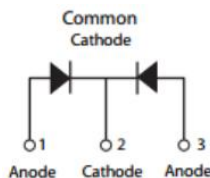
MBRF3035CT /MBRF3040CT /MBRF3045CT SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V _{RRM}	-	35	MBRF3035CT
Working Peak Reverse Voltage	V _{RWM}	-	40	MBRF3040CT
DC Blocking Voltage	V _R	-	45	MBRF3045CT
Average Rectified Forward Current	I _{F(AV)}	50% duty cycle @T _C =123 °C, rectangular wave form	15(per leg) 30(per device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3 ms, half Sine pulse	240	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop(Per Leg)*	V _{F1}	@ 15 A, Pulse, T _J = 25 °C	0.60	0.70	V
	V _{F2}	@ 30 A, Pulse, T _J = 25 °C	0.8	0.84	V
	V _{F2}	@ 15 A, Pulse, T _J = 125 °C	0.55	0.57	V
	V _{F2}	@ 30 A, Pulse, T _J = 125 °C	0.73	0.75	V
Reverse Current(Per Leg)*	I _{R1}	@V _R = rated V _R , T _C = 25 °C	0.03	1.0	mA
	I _{R2}	@V _R = rated V _R , T _C = 125 °C	15	100	mA
Junction Capacitance(Per Leg)	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	300	800	pF
Series Inductance(Per Leg)	L _S	Measured lead to lead 5 mm from package body	7.5	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	°C
Storage Temperature	T_{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	2.4	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

Ratings and Characteristics Curves

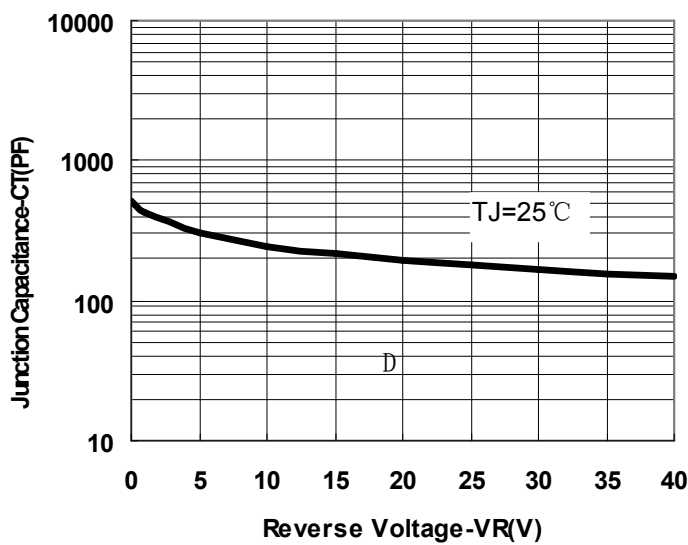


Fig.1-Typical Junction Capacitance

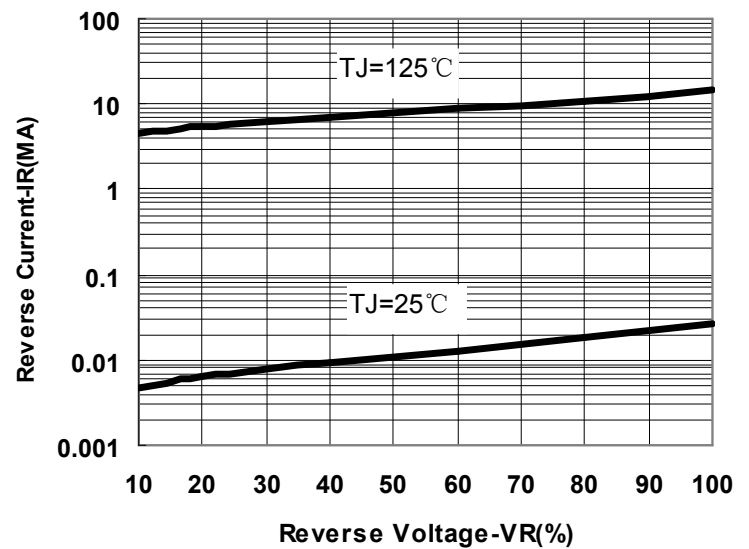


Fig.2-Typical Reverse Characteristics

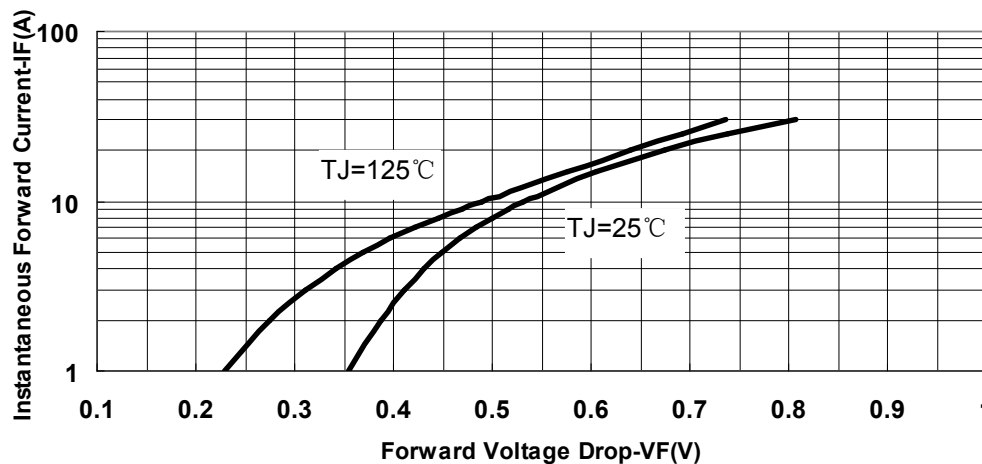
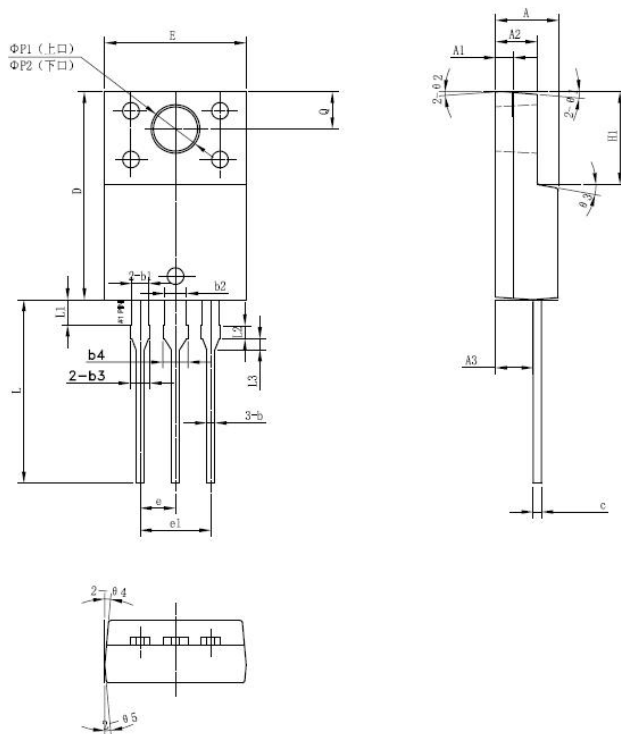


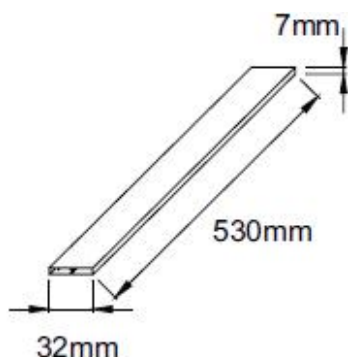
Fig.3-Typical Instantaneous Forward Voltage Characteristics

Mechanical Dimensions ITO-220AB

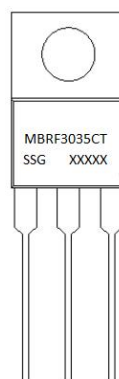


SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
c	0.50	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上口)	3.30	3.50	3.70
ΦP2(下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

MBR = Device Type
 F = Package type
 30 = Forward Current (30A)
 35 = Reverse Voltage (35V)
 CT = Configuration
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
MBRF3035(40)(45)CT	ITO-220AB (Pb-Free)	50 pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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